

2SD2321

Silicon NPN epitaxial planer type

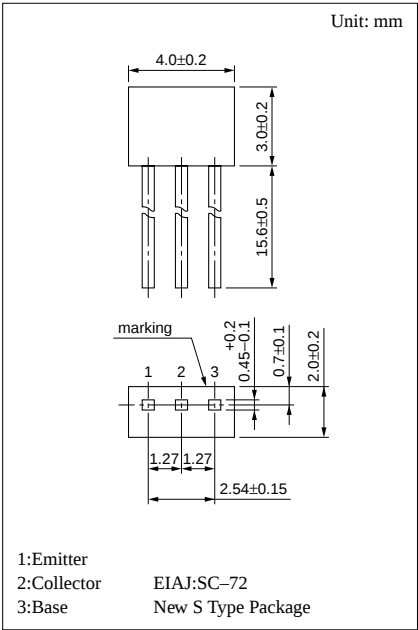
For low-frequency power amplification

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Satisfactory operation performances at high efficiency with the low-voltage power supply.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	40	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	5	A
Peak collector current	I_{CP}	8	A
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C



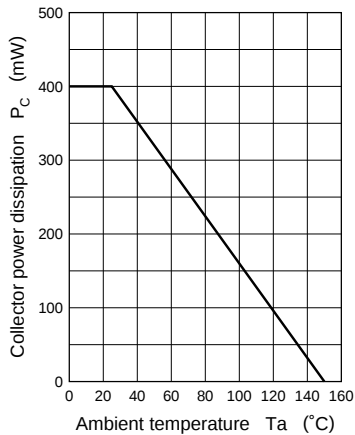
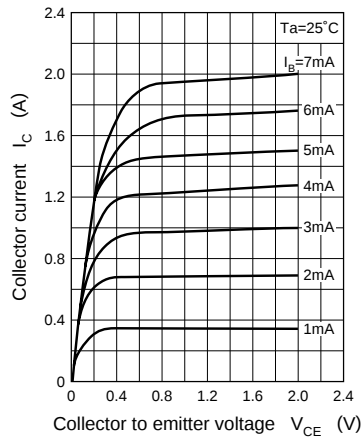
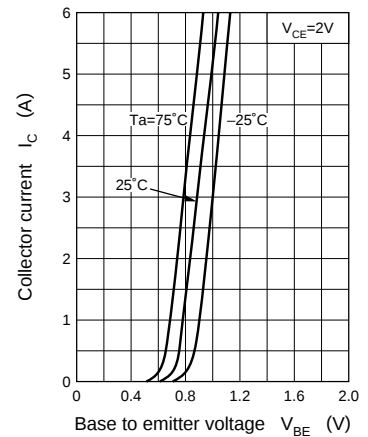
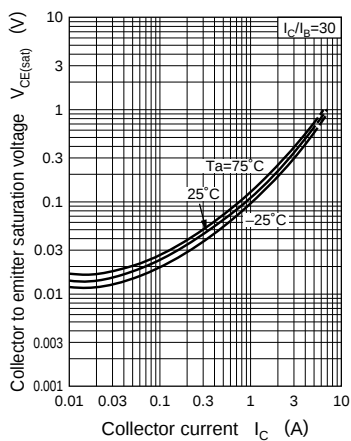
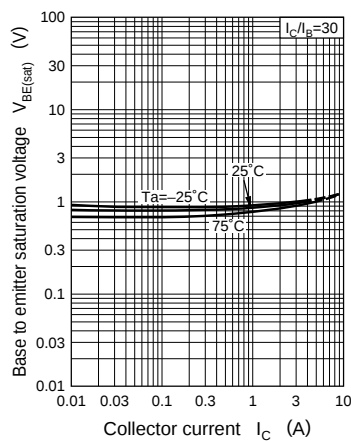
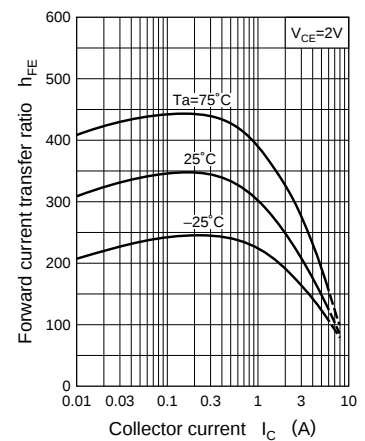
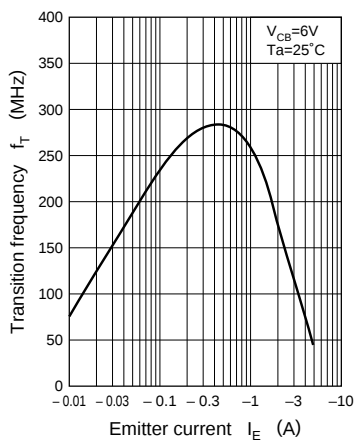
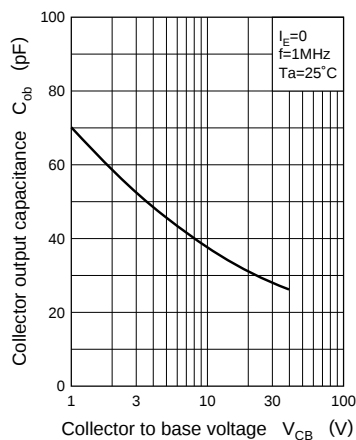
Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 10V, I_E = 0$			0.1	μA
	I_{CEO}	$V_{CE} = 10V, I_B = 0$			1.0	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 7V, I_C = 0$			0.1	μA
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	20			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	7			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = 2V, I_C = 0.5A^{*2}$	230		600	
	h_{FE2}	$V_{CE} = 2V, I_C = 2A^{*2}$	150			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 0.1A^{*2}$		0.28	1.0	V
Transition frequency	f_T	$V_{CB} = 6V, I_E = -50mA, f = 200MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 20V, I_E = 0, f = 1MHz$		26	50	pF

*2 Pulse measurement

*1 h_{FE1} Rank classification

Rank	Q	R
h_{FE1}	230 ~ 380	340 ~ 600

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 

Area of safe operation (ASO)

